

PROGRAMMABLE OVERVOLTAGE PROTECTOR

DESCRIPTION:



The ALPSVG170D is a Dual Programmable transient suppressor designed to protect against over voltages on the transmission equipment. Over voltages can be caused by lightning, AC power contact and induction. Dynamic protection performance is specified under typical international surge waveforms from Telcordia GR-1089-CORE, ITU-T K.44 and YD/T 950.

FEATURES:

- Dual Programmable transient suppressor
- ➤ Wide negative firing voltage range: V_{GKRM}= -167V max
- Low dynamic switching voltage: V_{FRM} and V_{GK(BO)}
- Low gate triggering current: I_{GT}=5mA max
- Peak pulse current: I_{PP}=30A for 10/1000μs surge
- ➤ Holding current: I_H=150mA min

APPLICATIONS:

- > T-1/E-1, ISDN, and xDSL transmission equipment
- Telecommunications infrastructure
- PBX's and other switches
- Set-top box
- ➢ VolP



MAXIMUM RATINGS

MAXIMUM RATINGS @ T_A = 25 °C unless otherwise specified				
PARAMETER	SYMBOL	RATINGS	UNIT	
Non-repetitive peak impulse current (1, 2)				
10/1000μS (Telcordia GR-1089-CORE)	I _{PPSM}	30	A	
5/310μS (ITU-T K.20, K.21, K.45, K.44 wave shape 10/700s)	1PPSIMI	40	,,	
2/10μS (Telcordia GR-1089-CORE)		120		
Non-repetitive peak on-state current, 50 Hz / 60 Hz (1, 2, 3)				
0.5s		6.5		
1s	I _{TSM}	4.5	A	
5s	IISM	2.4	^	
30s		1.3		
900s		0.72		
Repetitive peak off-state voltage, V _{GK} = 0	V_{DRM}	-170	V	
Repetitive peak gate-cathode voltage, V _{KA} = 0	$V_{\sf GKRM}$	-167	V	
Operating free-air temperature range	T _A	-40 to +85	°C	
Operating Junction Temperature	Tı	-40 to +150	°C	
Storage Temperature Range	T_{STG}	-40 to +150	°C	
Maximum lead temperature for soldering during 10s	T∟	260	°C	
Junction to free air thermal resistance (4)	$R_{ heta JA}$	120	°C/W	

Note:

- 1. Initially the device must be in thermal equilibrium with T_J = 25 °C. The surge may be repeated after the device returns to its initial conditions.
- 2. The rated current values may be applied to either of the Line to Ground terminal pairs. Additionally, both terminal pairs may have their rated current values applied simultaneously (in this case the Ground terminal current will be twice the rated current value of a single terminal pair.
- 3. Values for $V_{GG} = -100 \text{ V}$
- 4. EIA/JESD51-3 PCB, EIA/JESD51-2 environment, PTOT = 1.7 W



beyond boundaries...

ELECTRICAL CHARACTERISTICS @ TA = 25 °C unless otherwise specified

PARAMETER	CONDITIONS	SYMBOL	MIN	TYP.	MAX	UNIT
Forward Voltage	I _F =5A, t _W =200μs	V _F			3	٧
Peak forward recovery voltage	2/10μs, I _F =100A, R _S =50Ω, di/dt=80A/μs ⁽⁵⁾	V_{FRM}			10	٧
Off-state current	V _D =-170V, V _{GK} =0 T _J =25°C T _J =85°C	I _D			-5 -50	μΑ
Breakover voltage	$2/10$ μs, I_{TM} =-100A, R_s =50Ω, di/dt=-80A/μs, V_{GG} =-100V	V _(BO)			-112	V
Holding current	I _T =-1A, di/dt=1A/ms, V _{GG} =-100V	lн	-150			mA
Gate reverse current	V _{GG} =V _{GK} =-167V, V _{KA} =0 T _J =25°C T _J =85°C	I _{GKS}			-5 -50	μΑ
Gate trigger current	I _T =-3A, tp(g)≥20μs, V _{GG} =-100V	lgт			5	mA
Gate-Cathode trigger voltage	I _T =-3A, tp(g)≥20μs, V _{GG} =-100V	V _{GT}			2.5	V
Anode-cathode offstate capacitance	F=1MHz, V _d =1V, I _G =0 ⁽⁶⁾ V _D =-3V V _D =-48V	Сак			110 55	pF



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TYPICAL DEVICE RATING AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)

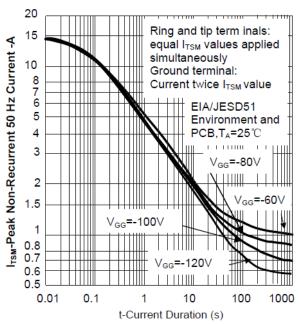


Fig.1 NON-REPETITIVE PEAK ON-STATE CURRENT VS
CURRENT DURATION

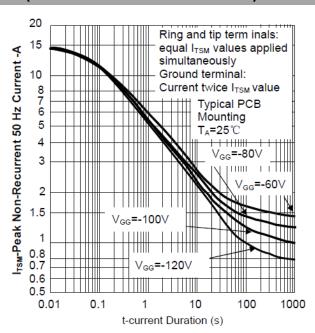


Fig.2 TYPICAL NON-REPETITIVE PEAK ON-STATE

CURRENT

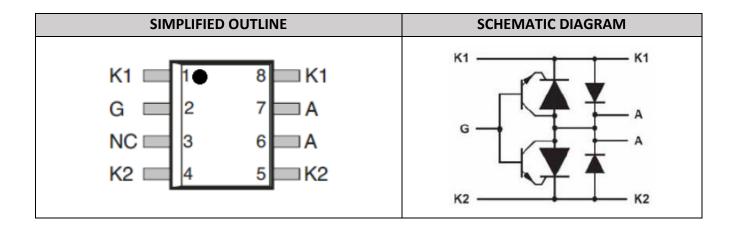
VS

CURRENT DURATION



beyond boundaries...

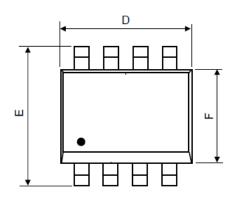
PINNING INFORMATION

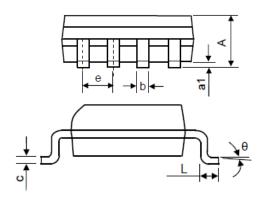




PACKAGE INFORMATION

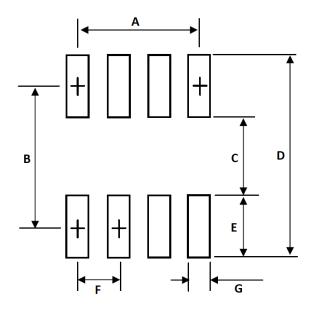
SOP-8





OUTLINE DIMENSIONS				
CVMADOL	MILLIMETERS			
SYMBOL	MIN	MAX		
А	1.35	1.75		
a1	0.10	0.25		
D	4.80	5.20		
Е	5.80	6.20		
F	3.80	4.00		
b	0.33	0.51		
е	1.27BSC			
С	0.17	0.25		
L	0.40	1.27		
θ	0°	8°		

SUGGESTED SOLDER PAD LAYOUT



OUTLINE DIMENSIONS		
SYMBOL	MILLIMETERS	
Α	3.81	
В	5.20	
С	3.00	
D	7.40	
Е	2.20	
F	1.27	
G	0.60	

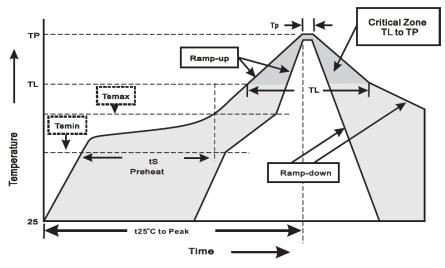
Note:

- 1. Controlling dimension: in millimeters.
- 2. General tolerance: ±0.05mm
- 3. The pad layout is for reference purposes only.

SOLDERING PARAMETERS

SUGGESTED THERMAL PROFILES FOR SOLDERING PROCESSES

- 1. Storage environment: Temperature=5 °C~40 °C Humidity=55% ±25%
- 2. Reflow soldering of surface-mount devices



3. Reflow soldering

PROFILE FEATURE	SOLDERING CONDITION
Average ramp-up rate (T _L to T _P)	<3 °C/sec
Preheat	
- Temperature Min (T _{smin})	150 °C
- Temperature Max (T _{smax})	200 °C
- Time (min to max) (t₅)	60 ~ 120 sec
T _{smax} to T _L	
- Ramp-upRate	<3 °C/sec
Time maintained above:	
- Temperature (T _L)	217 °C
- Time(tL)	60 ~ 260 sec
Peak Temperature (T _P)	255 °C-0/+5 °C
Time within 5 °C of actual Peak	10 ~ 30 sec
Temperature(tP)	
Ramp-down Rate	<6 °C/sec
Time 25 °C to Peak Temperature	<6 minutes



CUSTOMER NOTE:

DISCLAIMER

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- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).



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